

## **AMENDMENTS TO THE SPECIFICATION**

Please replace Paragraph [0079] with the following paragraph rewritten in amendment format:

**[0079]** However, when a precursor containing an amino functional group such as TEMAH is used to form the HfO<sub>2</sub> layer, nitrogen can be included in the resulting thin film without implementing a subsequent heat treatment. For example, it has been reported that an HfO<sub>2</sub> thin film formed using a LPCVD method using ~~TEDAH~~ TDEAH [Hf(N(C<sub>2</sub>H<sub>5</sub>)<sub>2</sub>)<sub>4</sub>] and O<sub>2</sub>, contains about 7% nitrogen.